

# Unveiling the Hard Anodization Regime of Aluminum: Insight into the Nanopore Self-Organization and Growth Mechanism

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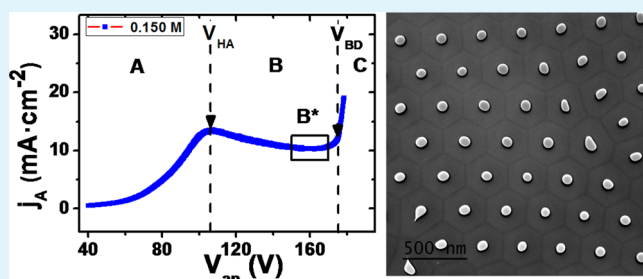
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## Supporting Information

**ABSTRACT:** The pore growth mechanism and its self-ordering conditions are investigated for nanoporous alumina membranes synthesized by hard anodization (HA) of Al in a broad range of anodic conditions, covering oxalic acid electrolytes with concentrations from 0.300 M down to 0.075 M and potentiostatic anodization voltages between 120 and 225 V. The use of linear sweep voltammetry (LSV) and scanning and transmission electron microscopy, together with image analysis techniques allow one to characterize the intrinsic nature of the HA regime. HA of aluminum is explained on the basis of a phenomenological model taking into account the role of oxalate ions and their limited diffusion through alumina nanochannels from a bulk electrolyte. The depletion of oxalate ions at the bottom of the pores causes an increased growth of the alumina barrier layer at the oxide/electrolyte interface. Furthermore, an innovative method has been developed for the determination of the HA conditions leading to self-ordered pore growth in any given electrolyte, thus allowing one to extend the available range of interpore distances of the highly ordered hexagonal pore arrangement in a wide range of 240–507 nm, while keeping small pore diameters of 50–60 nm.

**KEYWORDS:** hard anodization, self-organization, diffusion limited reaction, anodic aluminum oxide, nanoporous alumina



## INTRODUCTION

The novel opportunity of synthesizing self-ordered nanoporous anodic aluminum oxide (AAO) membranes with a high quality of the hexagonal pore arrangement by means of hard anodization (HA) has drawn a renewed interest in the development of innovative applications for such nanoporous structures, as well as to the spread of the current applications in conventional mild anodization (MA) to this new kind of nanoporous alumina templates. The intrinsic characteristics of this outstanding electrochemical fabrication method, such as its short processing time (1–5 h compared to the 24 to 48 h typical for the MA), high throughput, enhanced chemical and mechanical properties, and large range of available self-ordering conditions,<sup>1,2</sup> can be advantageous when compared with those of MA.

The short processing times necessary for the fabrication of hard anodic aluminum oxide (H-AAO) membranes arise from the fast nanoporous oxide growth rates of about 40 up to 80  $\mu\text{m}\cdot\text{h}^{-1}$  compared to the 1 up to 3  $\mu\text{m}\cdot\text{h}^{-1}$  obtained for conventional mild anodic aluminum oxide (M-AAO) grown in oxalic acid electrolytes under similar temperature conditions. In

addition, it is remarkable that there is a possibility of obtaining 50 high quality self-ordered pore arrangements in a fast single HA 51 step,<sup>2–4</sup> contrary to the well-established two-step MA process,<sup>5</sup> 52 which needs a long first anodization step in order to develop a 53 highly ordered pore arrangement. Finally, nanoporous AAO 54 membranes exhibiting well-ordered porous structures through 55 the whole membrane thickness can also be obtained by a two- 56 step approach under some specific HA conditions or by a 57 combination with suitable mild anodization.<sup>6,7</sup> HA methods 58 also provide the possibility of obtaining a wider range of 59 interpore distances within the self-organized pore regime than 60 those obtained in M-AAO. Indeed, interpore distance values 61 between 70 and 450 nm are achievable by HA using 62 appropriate anodizing electrolytic baths.<sup>8,9</sup> H-AAO membranes 63 display some interesting additional features that provide extra 64 freedom degrees for the manufacture of patterned templates 65 with tunable geometries. It has been reported that not only the 66

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67 anodization voltage but also the anodization current density  
68 exerts a significant influence on modifying the alumina barrier  
69 layer thickness, pore diameter, interpore distance, and spatial  
70 periodic ordering degree of the close-packed nanopore  
71 arrangement.<sup>2,8,10</sup> The ability to control these parameters  
72 independently may confer a high versatility to this process with  
73 respect to MA in order to tune all geometrical parameters of  
74 the AAO at will and in a much wider range. Recently, we have  
75 successfully applied the HA process in combination with  
76 interference lithography to produce perfectly ordered AAO  
77 membranes, demonstrating that the versatility of the HA was  
78 crucial to achieving perfect pore arrangement through large  
79 surface area membranes.<sup>11</sup> Additionally, it has been shown that  
80 HA can be used in combination with MA in sequential or  
81 pulsed processes, thus opening the door for the fabrication of  
82 new tailor-designed nanomaterials with complex three-dimen-  
83 sional structures.<sup>2,12–21</sup>

84 Despite the mentioned potential advantages of HA of  
85 aluminum in comparison with the conventional MA approach,  
86 it presents some disadvantages and technical difficulties,  
87 including the high tendency to show dielectric breakdown  
88 phenomena and need of high cooling power in order to  
89 dissipate the large amount of heat associated with high current  
90 densities (as high as  $200 \text{ mA}\cdot\text{cm}^{-2}$ ) characteristic of HA. The  
91 HA method has been successfully performed in several  
92 electrolytes comprising sulfuric<sup>1</sup> and oxalic acids<sup>2</sup> and mixtures  
93 between these acids.<sup>8,22</sup> The use of additives such as  
94 ethanol<sup>10,15</sup> and aluminum sulfate<sup>23</sup> or oxalate<sup>24</sup> is common,  
95 in order to stabilize the anodization process and to avoid the  
96 dielectric breakdown of the anodic oxide layer. A comple-  
97 mentary and well-established approach is to perform a  
98 preanodization step under MA conditions, followed by a linear  
99 sweep of the anodization voltage up to reach potentiostatic HA  
100 conditions, resulting in flat and smooth H-AAO membranes.<sup>2,4</sup>  
101 This prevents the high anodic current densities that appear  
102 during the first stages of the HA, which are responsible for local  
103 catastrophic burning phenomena.

104 There is, however, a substantial lack of scientific and  
105 technical knowledge about the nature of the HA processes,  
106 the nanopore growth mechanism and self-ordering conditions,  
107 and the relevant technical possibilities of nanofabrication  
108 offered by this novel electrochemical technique. The exper-  
109 imental correlations found in the case of MA between the self-  
110 organization of pores, governed by the local electric field, and  
111 the geometric parameters of the pores have been missing for  
112 HA. A complete understanding of the HA process would  
113 facilitate the application of this technique for the fabrication of  
114 nanoporous membranes with tailored geometry, which are  
115 highly appreciated in nanoscience and nanotechnology for a  
116 broad spectrum of applications ranging from chemical and  
117 biochemical sensors,<sup>25–28</sup> nanofiltration,<sup>29</sup> drug delivery,<sup>30</sup>  
118 superhydrophobic surfaces,<sup>31</sup> and nanogenerators,<sup>32–34</sup> among  
119 many others.

120 In the present work, we report on a systematic study of the  
121 HA process and the nanopore self-ordering regime in oxalic  
122 acid electrolytes, covering a wide range of anodic conditions  
123 (electrolyte concentration and anodic voltage). A detailed  
124 characterization of the morphological features of H-AAO  
125 membranes is performed as a function of the synthesis  
126 conditions, shedding light into the intrinsic nature of HA  
127 processes. The analysis of the main features of the anodic  
128 oxidation of Al in oxalic acid electrolytes with varying  
129 concentration is carried out based on a LSV study performed

in a wide voltage range from 40 V up to 250 V, which enables  
one to determine the HA voltage intervals leading to stable  
hard anodization conditions. Consequently, a correlation of  
LSV curves with the self-ordered growth of the nanopore  
arrangements is determined for the studied electrolytes. In  
addition, potentiostatic hard anodization experiments have  
been carried out under different experimental conditions, and  
the data collected from scanning and transmission electron  
microscopy characterization, in combination with the analysis  
of the corresponding anodization current transients, were useful  
to understand the HA processes. The accurate study presented  
here, which involves a deep comprehension on the nature of  
HA processes, along with a careful analysis of the voltammetric  
curves, could provide a systematic procedure to determine the  
optimum HA self-ordering interval for other electrolytes, thus  
allowing for a continuous tuning of the geometrical character-  
istics of H-AAO membranes.

## ■ EXPERIMENTAL SECTION

High purity Al foils (Goodfellow, Al 99.999%), 2.5 cm in diameter and  
0.5 mm in thickness, were cleaned by sonication in isopropanol and  
ethanol. Prior to HA and voltammetric studies, the samples were  
loaded into a two-electrode anodization cell equipped with a 100 mL  
electrolyte reservoir, which exposes a sample area of  $2.54 \text{ cm}^2$  to the  
electrolyte. The cell includes a Cu back plate which is used to provide  
both electrical and thermal contact to the sample and a Pt counter-  
electrode. The Al foils were then electropolished in a mixture of  
perchloric acid and ethanol (1:3 vol.) at  $5^\circ\text{C}$  and 20 V. The  
electropolished Al foils were subsequently anodized under mild  
anodization conditions during 15 min (0.300 M oxalic acid solution at  
 $40 \text{ V}$  and  $3^\circ\text{C}$ ). Afterward, the oxalic acid (0.300 M) electrolyte was  
replaced with a renewed electrolyte having the desired oxalic acid and  
ethanol concentrations, and the anodization voltage was slowly swept  
from 40 V to the target HA voltage in the range of 100–250 V. A  
constant voltage sweep rate of  $0.02 \text{ V}\cdot\text{s}^{-1}$  was employed, unless a  
different sweep rate is specified in the text. In voltammetric  
measurements, the voltage was increased at the same sweep rate  
until the dielectric breakdown of the alumina barrier layer is evidenced  
by a sudden increase of the anodic current density.

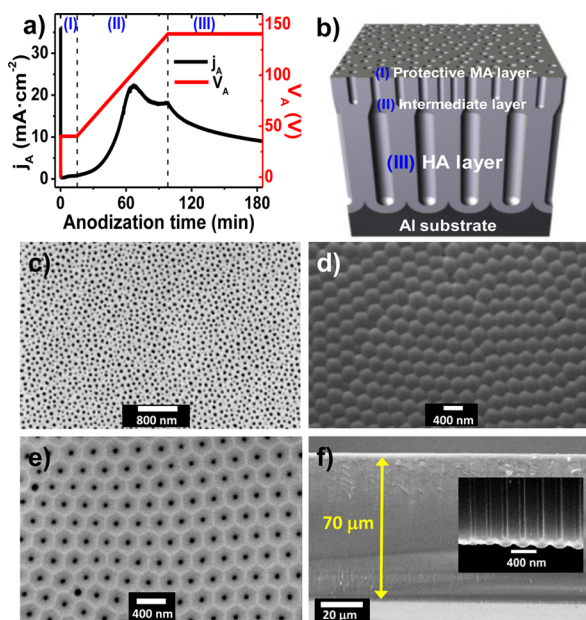
Both, HA processes and voltammetric studies were performed in  
oxalic acid electrolytes, with concentrations selected in the range  
between  $0.300 \pm 0.002 \text{ M}$  and  $0.075 \pm 0.002 \text{ M}$ , and containing a  
certain amount of ethanol (5–10 vol %), which acts as an antifreezing  
agent and contributes to dissipating the heat generated during the HA  
processes.<sup>8,10</sup> The concentration of ethanol was selected as the  
minimum addition that prevents electrolyte freezing, thus avoiding  
high ethanol concentrations that may deteriorate the quality of the H-  
AAO membranes.<sup>7</sup> The temperature of the electrolytes was adjusted in  
the range between  $-1$  to  $0^\circ\text{C}$  prior to the HA step, and it was  
maintained below  $3^\circ\text{C}$  by an external recirculating bath that  
refrigerates the copper back plate and the anodic electrode. The  
electrolytes were vigorously stirred during anodization, in order to  
ensure the homogeneity of the temperature and bulk electrolyte  
concentration within the anodization cell during the entire anodization  
process. The anodization voltages ( $V_{\text{an}}$ ), ranging from 40 to 250 V,  
were applied between the sample and the Pt counter electrode by a  
computer controlled power supply, whereas anodization current  
transients were monitored by means of a computer controlled digital  
multimeter. The reported values of the anodic current density,  $j_{\text{A}}$ , are  
obtained as the ratio between measured anodic current intensity and  
the total sample area, without considering the effective area of the  
porous alumina layer.

After the HA processes, the remaining Al substrate was removed by  
wet chemical etching in an aqueous solution of 0.14 M  $\text{CuCl}_2$  and 0.4  
M HCl. The alumina barrier layer at the bottom of the pores was  
removed by reactive ion etching (Sentech, SI 220) from the back of  
the AAO membranes in a plasma generated from a mixture of  $\text{O}_2$  and  
 $\text{CF}_4$  at 12 mTorr under an applied power of 250 W ( $0.8 \text{ W cm}^{-2}$ ). The

197 morphology of the back of the samples was studied by means of  
198 scanning electron microscopy (SEM, Supra 55-Zeiss). The determi-  
199 nation of the interpore distance ( $D_{int}$ ), pore diameters ( $D_p$ ), and  
200 barrier layer thicknesses ( $t_{BL}$ ) was performed by image analysis of  
201 bottom and cross-section view SEM micrographs using the image  
202 processing packages ImageJ, version 1.48 (NIH, USA), and WsXM,  
203 version 5.0 (Nanotec, Spain).<sup>35,36</sup> The microstructure of some of the  
204 samples was studied by TEM after reducing the membrane thickness  
205 to few nanometers by ion milling.

## 206 ■ RESULTS AND DISCUSSION

207 A characteristic current transient recorded during the H-AAO  
208 fabrication procedure is shown in Figure 1a, whereas some

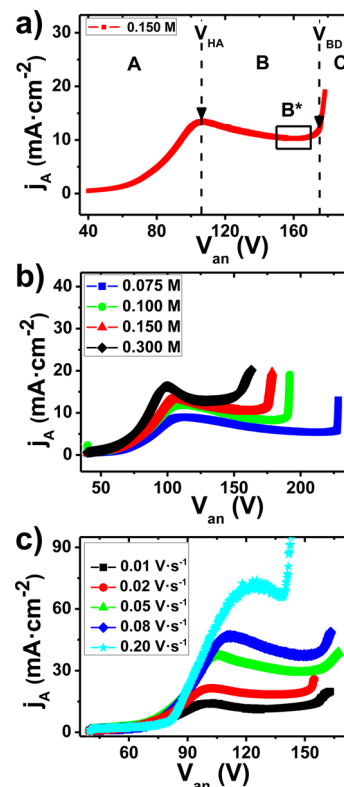


**Figure 1.** (a) Characteristic current and voltage transients recorded during the fabrication of an H-AAO membrane. (b) Schematic drawing of the H-AAO structure, indicating the protective MA layer at the top, the intermediate layer, and the highly ordered HA layer. (c–f) SEM images of H-AAO membranes. (c) Top view, showing the protective MA layer. (d) Bottom view, showing the high ordering degree in the bottom of the H-AAO. (e) Bottom view after removing the alumina barrier layer which blocks the bottom of the pores. (f) Cross-section view. The inset in f shows a magnification of the region close to the alumina barrier layer, evidencing that the pores grow parallel to each other during the HA process.

209 relevant SEM images of a H-AAO membrane are shown in  
210 Figure 1c–f. Three different stages corresponding to the  
211 employed anodization protocol can be distinguished in the  
212 current transient of Figure 1a, leading to the growth of three  
213 nanoporous layers with different morphologies indicated in  
214 Figure 1b. The initial potentiostatic MA step (I), showing the  
215 typical current transient, provides a first thick alumina layer  
216 with a dense and highly disordered porous structure showing a  
217 broad pore size distribution (Figure 1c). This layer acts as a  
218 protection for the HA step preventing undesired burning  
219 phenomena due to high current density flow. (II) During the  
220 linear voltage sweep, the anodization conditions are varied from  
221 MA (40 V) to the desired HA voltage (140 V in this particular  
222 case). An exponential increase of the current density is  
223 observed until a maximum is reached, after which the current  
224 decreases. During this step, a rearrangement of the pores takes  
225 place in order to accommodate their growth to the continuous

change of the anodization voltage.<sup>4</sup> (III) When the final HA  
226 voltage is reached and kept constant, a fast decrease of the  
227 anodization current density with time is observed. This has  
228 been attributed to the rapid increase of the nanopores length,  
229 which lengthens the diffusion path of the ionic species involved  
230 in the electrochemical reaction.<sup>2,4</sup> During the anodization stage  
231 (III), the pores are uniform in size, and they grow parallel to  
232 each other, following a highly ordered hexagonal arrangement,  
233 as can be observed in Figures 1d and e, and in the inset of  
234 Figure 1f. An average growth rate of about 50  $\mu\text{m}/\text{h}$  can be  
235 roughly estimated from Figure 1f, which corresponds to a cross-  
236 section view of a membrane anodized under hard anodization  
237 conditions during 1.5 h. This value is reduced to around 25  
238  $\mu\text{m}/\text{h}$  when the duration of the whole process, i.e., MA and  
239 voltage ramp steps, is taken into account. However, the AAO  
240 nanoporous layer growth rate does not keep constant during  
241 the entire HA process, and therefore, the H-AAO membrane  
242 thickness does not increase linearly with the anodization time,  
243 as evidenced in Figure S1 (Supporting Information) and  
244 explained in detail in the following sections. 245

**Voltammetric Studies of the Anodic Oxidation of**  
246 **Aluminum.** Figure 2a shows a typical LSV measured at a  
247 sweep rate of 0.02  $\text{V}\cdot\text{s}^{-1}$  during the anodic oxidation of Al in a  
248



**Figure 2.** (a) LSV of the anodic oxidation behavior of Al in 0.15 M oxalic acid electrolyte containing 5 vol % of ethanol. The different stages are labeled as A (mild anodization regime), B (hard anodization regime), B\* (current plateau), and C (dielectric breakdown). The voltage values  $V_{HA}$  and  $V_{BD}$  indicate the beginning of the HA regime and the dielectric breakdown of the anodic oxide, respectively. (b) LSV characteristic of the anodic oxidation of Al in several electrolytes with different oxalic acid concentrations ranging from 0.075 to 0.300 M and 5–10 vol % of ethanol. (c) LSV of the anodic oxidation of Al in 0.3 M oxalic acid electrolyte and 5 vol % of ethanol obtained at different voltage sweeping rates.



249 0.15 M oxalic acid electrolyte containing 5 vol % of ethanol.  
 250 Three different regions, respectively labeled as A, B, and C, can  
 251 be clearly distinguished. In region A, corresponding to low  
 252 values of the applied anodization voltage (40–106 V), the  
 253 anodic current density,  $j_A$ , increases monotonously with  
 254 increasing anodization voltage. This current increase is in  
 255 agreement with the high-field conduction theory well  
 256 established for MA processes, which relates the anodic current  
 257 density with the potential drop across the barrier layer,  $\Delta V_{BL}$ ,  
 258 through eq 1:

$$259 \quad j_A = j_0 e^{(\beta \Delta V_{BL} / t_{BL})} \quad (1)$$

260 where  $t_{BL}$  the barrier layer thickness. The parameters  $\beta$  and  $j_0$   
 261 depend on the material and anodic conditions of the  
 262 experiment and change with temperature as  $T^{-1}$  and  $e^{-1/T}$ ,  
 263 respectively.<sup>2,20,37–40</sup> Therefore, in region A, which corresponds  
 264 to the MA regime, the current density is limited by the electric  
 265 field-driven ion migration across the oxide barrier layer. This  
 266 expression is also in good agreement with the classical  
 267 explanation of the current transients during the potentiostatic  
 268 MA of aluminum, in which the different stages of the  
 269 anodization process are correlated with changes in the barrier  
 270 layer thickness due to the competition between oxidation and  
 271 dissolution processes.<sup>41–43</sup>

272 The transition between regions A and B in Figure 2a is  
 273 delimited by the presence of a local maximum of the current  
 274 density at a certain value of the anodic voltage  $V_{an} = V_{HA}$ , which  
 275 can be ascribed to the beginning of the HA regime, as it will be  
 276 discussed below. Further increases of the anodic voltage result  
 277 in lower anodic current densities, an indication that the current  
 278 density-limiting mechanism has changed. In fact, it has been  
 279 stated that during potentiostatic HA processes, the fast growth  
 280 of the nanopores causes an exponential current decrease (see  
 281 Figure 1a). This effect has been related to a diffusion limiting  
 282 mechanism due to the increasing diffusion length with the pore  
 283 growth for the ionic species involved in the anodic oxidation of  
 284 Al.<sup>2–4</sup> However, to the best of our knowledge, a direct  
 285 experimental demonstration of this interpretation has not yet  
 286 been shown in the literature so far.

287 The HA region (labeled as B in Figure 2a) can be considered  
 288 to extend from  $V_{HA}$  up to a certain voltage value,  $V_{BD}$ , at which  
 289 the anodic current density dramatically increases. This is due to  
 290 the dielectric breakdown of the alumina barrier layer as a result  
 291 of the high electric field. Dielectric breakdown is accompanied  
 292 by an intense heat generation causing a catastrophic damage of  
 293 the nanoporous membrane, ascribed to the following region C.  
 294 The presence of a current plateau can be also observed in  
 295 region B of Figure 2a. Therefore, region  $B^*$  is defined as a  
 296 voltage range of 20 to 30 V around the minimum current  
 297 density value of the plateau region. A similar behavior was  
 298 observed in electrolytes with different oxalic acid concen-  
 299 trations, ranging from 0.075 to 0.300 M (Figure 2b). The  
 300 characteristic values of  $V_{HA}$ ,  $V_{BD}$ , and  $B^*$  for each electrolyte  
 301 concentration are displayed in Table 1. The selected value for  
 302 the voltage sweep rate employed in the LSV experiments (0.02  
 303  $V \cdot s^{-1}$  in all of the previous measurements) can also modify the  
 304 resulting curves. The effect of employing different voltage  
 305 sweep rates is evidenced from Figure 2c, which shows LSV  
 306 obtained at sweep rates ranging from 0.01 to 0.2  $V \cdot s^{-1}$  in 0.3 M  
 307 oxalic acid electrolyte with 5 vol % ethanol. The nonreversible  
 308 formation of a porous AAO layer onto the anode surface affects  
 309 ion transport to the reaction interface, decreasing both the

**Table 1. Characteristic Values of  $V_{HA}$ ,  $V_{BD}$ , and Voltage Range of the  $B^*$  Plateau Interval, Obtained from LSV in Oxalic Acid Electrolytes with Concentrations Ranging from 0.075 to 0.300 M, Containing 5–10 vol. % Ethanol**

$[(COOH)_2]$ (M)	ethanol (vol %)	$V_{HA}$ (V)	$B^*$ range (V)	$V_{BD}$ (V)
$0.300 \pm 0.002$	$5.0 \pm 0.1$	$100 \pm 1$	120–150	$153 \pm 1$
$0.150 \pm 0.002$	$5.0 \pm 0.1$	$106 \pm 1$	150–170	$175 \pm 1$
$0.100 \pm 0.002$	$10.0 \pm 0.1$	$112 \pm 1$	160–190	$190 \pm 1$
$0.075 \pm 0.002$	$10.0 \pm 0.1$	$114 \pm 1$	190–225	$226 \pm 1$

anodic current density and  $V_{HA}$  value as the sweep rate is 310  
 reduced. Despite these differences, all of the LSV curves display 311  
 features similar to those discussed for Figure 2a, except for the 312  
 curve corresponding to a sweep rate of 0.2  $V \cdot s^{-1}$ , which shows a 313  
 $V_{BD}$  voltage of 138 V, noticeably smaller than that of the curves 314  
 recorded at slower voltage sweep rates, indicating that low 315  
 sweep rates are more adequate to study HA processes. 316

In both, Table 1 and Figure 2b, the influence of the oxalic 317  
 acid concentration on the  $j_A(V_{an})$  curves can be observed. The 318  
 voltage value of  $V_{HA}$  (i.e., the value of the anodic voltage at 319  
 which the HA regime starts) shifts to higher anodic voltages as 320  
 the oxalic acid concentration decreases. A similar trend can be 321  
 also observed for the other characteristic parameters,  $B^*$  and 322  
 $V_{BD}$ . Additionally, the anodic current density for a given anodic 323  
 voltage decreases as the oxalic acid concentration is reduced. 324  
 These observations indicate that the behavior of Al anodic 325  
 oxidation and particularly that of the HA regime can be 326  
 controlled by carefully selecting the electrolyte oxalic acid 327  
 concentration. 328

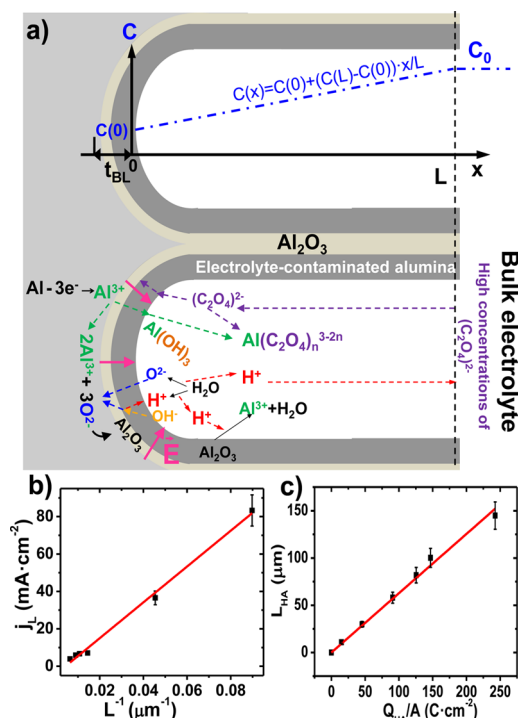
**Mechanism of Hard Anodization Processes.** As it has 329  
 been previously mentioned, HA of Al is generally ascribed to a 330  
 diffusion-limited process due to the increased diffusion length 331  
 of the ionic species involved in the anodic electrochemical 332  
 reactions, as a consequence of the fast growth rate exhibited by 333  
 H-AAO membranes.<sup>2–4</sup> On the contrary, the growth of the 334  
 AAO membrane during the MA process, is usually slower. 335  
 Therefore, no limited diffusion regime is established for any of 336  
 the ionic species involved in the MA electrochemical reactions. 337  
 The ionic flux through a nanoporous membrane of porosity  $P$  338  
 and thickness  $L$  is given by the extended Nernst–Planck 339  
 equation for the ionic transport (eq 2).<sup>44–46</sup> 340

$$341 \quad J = -PD \frac{\partial C(x)}{\partial x} - \frac{zFP}{RT} DC(x) \frac{\partial V(x)}{\partial x} + PC(x)v_{eo}(x);$$

$$(0 \leq x \leq L) \quad (2)$$

where  $x$  represents the distance to the reaction interface, that is, 342  
 to the pore bottom,  $D$  is the diffusion coefficient of the specific 343  
 ion of interest, and  $C(x)$  corresponds to its concentration and  $z$  344  
 to its charge number.  $R$  and  $F$  are ideal gas and Faraday 345  
 constants, respectively,  $V(x)$  is the electric potential inside the 346  
 pores and  $v_{eo}$  is the solution velocity due to convection. The 347  
 first, second, and third terms in eq 2 correspond to diffusion, 348  
 migration, and convection contributions to ionic transport, 349  
 respectively. Despite the high stirring rates employed in our 350  
 experiments, which cause intense forced convection in the bulk 351  
 of the electrolyte, as a first approximation the contribution of 352  
 this term inside the pore channels ( $0 \leq x \leq L$ ) is considered to 353  
 be negligible due to electrolyte confinement in the nanoporous 354  
 medium. Furthermore, the presence of high mobility  $H^+$  ions 355  
 assures the high electric conductivity of the electrolyte. 356  
 Therefore, the electric potential drop through the pore 357

channels is considered to be small in comparison with that at the bottom of the pores due to the highly resistive alumina barrier layer.<sup>20,47,48</sup> Therefore, migration is neglected, and only the first term in eq 2, associated with diffusion contribution to ion transport, will be considered in our simple model. Assuming that the electrolyte ions exhibit a linear diffusion profile along a constant concentration gradient between the pore bottom and the bulk of the electrolyte (see Figure 3a), the ion concentration can then be written as  $C(x) = C(0) + [C(L) - C(0)]x/L$ .



**Figure 3.** (a) Schematic diagram of the chemical and electrochemical reactions taking place during aluminum anodization in oxalic acid electrolytes (lower pore), and linear profile of the concentration gradient (upper pore) along the pore length. (b) Fitting of the final anodization current density,  $j_L$ , as a function of the inverse of the total membrane thickness,  $L$ , obtained for H-AAO samples anodized at 120 V in 0.300 M oxalic acid electrolyte. (c) Thickness of H-AAO layers,  $L_{HAO}$ , grown by anodization in 0.3 M oxalic acid at 120 V, as a function of the HA charge density,  $Q_{HA}/A$ ,  $A$  being the area of the aluminum electrode.

If the electrochemical reaction is limited by the transport of ions from the electrolyte, we can state that the concentration of these particular ions at the reaction interface is negligible, and therefore  $C(0) = 0$ , while  $C(L)$  can be assumed to be equal to the initial concentration of the bulk electrolyte,  $C_0$ , kept constant by the vigorous stirring employed during the whole anodization process. Thus, the diffusion-limited current density,  $j_{DL}$ , can be approximated by eq 3.

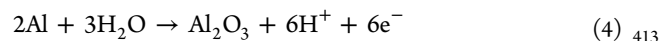
$$j_{DL} = |zFj| = \frac{zPFDC_0}{L} \quad (3)$$

Therefore, a diffusion-limited mechanism will be associated with an inverse dependence of the anodization current density on the membrane thickness. It is worth mentioning that more sophisticated models that include a nonzero but constant electric field within the pore channels (Goldman constant-field

approximation)<sup>49</sup> would also result in an inverse relationship between the anodization current density and the membrane thickness for the case of diffusion-limited electrochemical reactions.<sup>50</sup>

In order to verify whether or not this is the actual behavior of the HA current transients, a series of samples were fabricated in oxalic acid 0.300 M containing 5 vol % of ethanol, at an HA voltage of 120 V (voltage sweep rate of 0.2 V·s<sup>-1</sup>). Different time interval durations of the potentiostatic HA step varying from 0 s up to 36000 s were employed. The final anodization current density (that is, the last current density value recorded during the anodization), henceforth called  $j_L$ , is depicted in Figure 3b as a function of the inverse of the total AAO membrane thickness measured from SEM images. A linear dependence of  $j_L$  on  $L^{-1}$  is clearly observed, demonstrating that HA can be considered as a diffusion controlled process, and hence,  $j_A = j_{DL}$ . Therefore, we can ascribe the local maximum in the  $j_A(V_{an})$  curve of Figure 2a as the beginning point of the HA regime, characterized by a diffusion-limited oxide growth. Figure 3c shows the dependence of the H-AAO layer thickness on the charge density flowing through the electrochemical cell during HA process, evidencing a linear relationship despite the nonconstant growth rate of H-AAO layers on time previously mentioned and illustrated in Figure S1.

From the previous results, a diffusion-limited mechanism has been demonstrated to dominate the anodic oxidation of Al during HA processes. However, it is still unclear which one of the ions involved in the anodic oxidation of Al is depleted at the reaction interface, thus limiting the anodization process. The overall anodic reaction occurring during the oxidation of aluminum is given by<sup>20,51</sup>



This global anodic reaction results from the different chemical and electrochemical reactions that take place at the metal/oxide (m/o) and oxide/electrolyte (o/e) interfaces, which are schematized in Figure 3a. At the m/o interface, metallic aluminum is oxidized to Al<sup>3+</sup> ions. Around 60% of the Al<sup>3+</sup> ions react with O<sup>2-</sup> anions extracted from the electrolyte at the o/e interface that reach the m/o interface by ionic migration across the alumina barrier layer, as a consequence of the intense electric field.<sup>20,52,53</sup> This reaction leads to the formation of Al<sub>2</sub>O<sub>3</sub> at the m/o interface, thus increasing the barrier layer thickness. The remaining 40% of Al<sup>3+</sup> ions migrate outward, and finally, they are ejected into the electrolyte at the o/e interface. Depending on the local chemical environment, ejected Al<sup>3+</sup> ions are complexed by electrolyte anions (i.e., oxalates), forming water-soluble complexes, or they react with OH<sup>-</sup> ions leading to the formation of aluminum hydroxides, which are further hydrolyzed resulting in redeposition of alumina at the o/e interface.<sup>52,54,55</sup> The Al<sub>2</sub>O<sub>3</sub> formation at the o/e interface plays an important role in the growth of barrier-type alumina layers. However, if this phenomenon is absent or reduced to an extent, alumina films develop a porous structure.<sup>20,52,56,57</sup> Additionally, chemical dissolution of alumina takes place also in the o/e interface.<sup>58-60</sup>

From all of the above-discussed chemical and electrochemical reactions, we can assume that the most probable ion to be depleted at the reaction o/e interface is the oxalate ion. The rest of the ions can be discarded since O<sup>2-</sup>, OH<sup>-</sup>, and H<sup>+</sup> ions are continuously generated from water molecules at this interface, and thus, they are unlikely to be depleted. In the same way, water is the most abundant chemical species in the

444 electrolyte since it is the solvent, while the Al substrate assures a  
 445 continuous supply of  $\text{Al}^{3+}$  ions. Additionally, the oxalate ions  
 446 play a crucial role in the development of nanoporous structures  
 447 during the electrochemical anodization of Al, even though they  
 448 are not directly involved in the electrochemical oxidation of  
 449 aluminum. In oxalic acid electrolytes, the fraction of  $\text{Al}^{3+}$  ions  
 450 that are ejected into the electrolyte as a consequence of the  
 451 field-driven ionic migration across the alumina barrier layer are  
 452 complexed by oxalate ions forming water-soluble molecules. In  
 453 a similar way, phosphate or sulfate ions bind  $\text{Al}^{3+}$  forming  
 454 soluble complex ions during Al anodization in phosphoric or  
 455 sulfuric acids, respectively. Therefore, during the anodization  
 456 process in pore-forming electrolytes, the growth of the alumina  
 457 layer takes place mainly at the m/o interface, and the  $\text{Al}^{3+}$  ions  
 458 ejected into the electrolyte do not have any important  
 459 contribution to Al oxide growth. However, in nonpore forming  
 460 electrolytes, such as borate, the  $\text{Al}^{3+}$  ions ejected into the  
 461 electrolyte do not form complexes. Depending on the anodic  
 462 conditions (pH, temperature, etc.), they lead to the formation  
 463 of aluminum hydroxides (i.e.,  $\text{Al}(\text{OH})_3$  and  $\text{Al}(\text{OH}_2)_6^{3+}$ ) which  
 464 are hydrolyzed forming alumina. As a consequence,  $\text{Al}_2\text{O}_3$   
 465 growth occurs at the same time in both o/e and m/o  
 466 interfaces.<sup>20,56,61</sup>

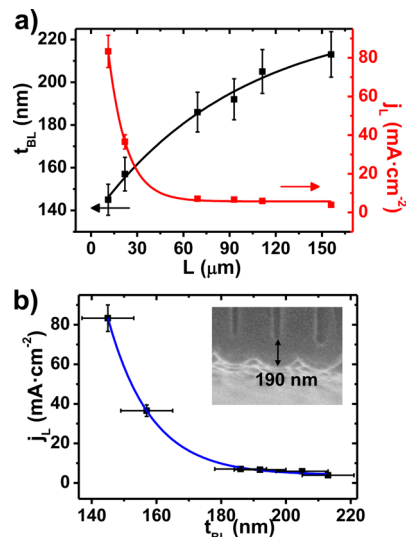
467 Therefore, it is possible to argue that during the HA of Al in  
 468 oxalic acid electrolytes, a fraction of the ejected  $\text{Al}^{3+}$  ions react  
 469 with oxalates at a rate that is determined by the ionic diffusion  
 470 of oxalate ions from the bulk of the electrolyte to the reaction  
 471 interface. The rest of  $\text{Al}^{3+}$  ions or at least a substantial fraction  
 472 of them react with hydroxides or water, forming nonsoluble  
 473 chemical species that finally contribute to the formation of  
 474  $\text{Al}_2\text{O}_3$  at the o/e interface. The redeposition of  $\text{Al}_2\text{O}_3$  at the o/e  
 475 interface might result in a noticeable thickening of the  $\text{Al}_2\text{O}_3$   
 476 barrier layer at the bottom of the pores and in a decrease of the  
 477 electric field strength across the barrier layer, given by  $\Delta V_{\text{BL}}/$   
 478  $t_{\text{BL}}$ , where  $\Delta V_{\text{BL}} \approx V_{\text{an}} = \text{cte}$ . The decrease in electric field  
 479 strength due to barrier thickening is responsible for the  
 480 progressive diminution of anodization current density and for  
 481 the nonlinearity of the H-AAO layer with the anodization time  
 482 shown in Figure S1.

483 **Experimental Validation of the HA Model.** In order to  
 484 verify the proposed mechanism for the HA processes, we have  
 485 systematically measured the thickness of the alumina barrier  
 486 layer,  $t_{\text{BL}}$ , at different time interval durations of the HA  
 487 potentiostatic step varying from 0 to 36000 s for samples  
 488 fabricated in 0.300 M oxalic acid containing 5 vol % of ethanol,  
 489 under an applied anodic voltage of 120 V.

490 Figure 4a illustrates the dependence of both, the alumina  
 491 barrier layer thickness and the limit current density,  $j_{\text{L}}$ , on the  
 492 total thickness,  $L$ , of the nanoporous alumina membranes. It  
 493 can be seen that, while  $t_{\text{BL}}$  increases with the membrane total  
 494 thickness,  $j_{\text{L}}$  decreases. This relationship between  $j_{\text{L}}$  and  $L$  is in  
 495 good agreement with eq 1 and therefore with the proposed HA  
 496 mechanism. In fact,  $t_{\text{BL}}$  and  $j_{\text{L}}$  are closely related, as can be  
 497 observed in Figure 4b. The limit current density,  $j_{\text{L}}$ , shows an  
 498 exponential dependence on  $t_{\text{BL}}$  that can be fitted through the  
 499 following phenomenological equation:

$$500 \quad j_{\text{L}} \approx 4 \cdot 10^6 \text{ mA cm}^{-2} e^{(13.4 \text{ nm} / t_{\text{BL}})} \quad (5)$$

501 By comparing eqs 1 and 5, we can see that the current  
 502 density still follows, in the case of HA processes, the  
 503 exponential dependence on the barrier layer thickness predicted  
 504 by the high-field conduction theory for MA,<sup>38</sup> with  $j_0 = 4 \times 10^6$



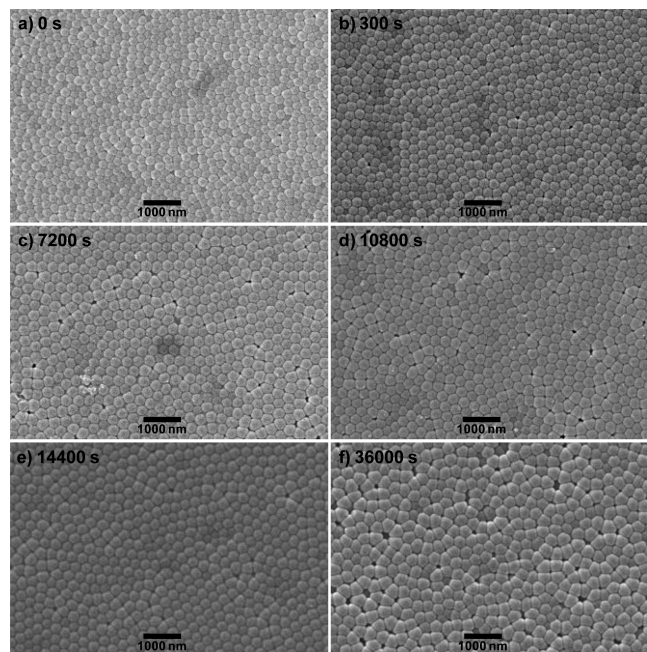
**Figure 4.** (a) Dependence of the barrier layer thickness,  $t_{\text{BL}}$ , and limit current density,  $j_{\text{L}}$ , on the total thickness of the alumina membrane. (b) Dependence of the limit current density on the alumina barrier layer thickness. The inset shows a SEM image of the alumina barrier layer of the sample anodized during 10800 s. All of the HAs were performed at 120 V in 0.300 M oxalic acid electrolyte containing 5 vol % of ethanol.

505  $\text{mA cm}^{-2}$  and  $\beta = 0.112 \text{ nm}\cdot\text{V}^{-1}$ . Therefore, other contributions  
 506 to the anodic current density, such as electron avalanche  
 507 multiplication,<sup>20,52</sup> are negligible or play a minor role during  
 508 HA processes as long as dielectric breakdown of the oxide layer  
 509 is avoided. Furthermore, the good agreement found between  
 510 eqs 1 and 5 employing temperature independent fitting  
 511 parameters points out that the heat generated due to the  
 512 high anodic current densities is successfully dissipated by the  
 513 refrigeration system. According to our experimental results, the  
 514 increase of the porous membrane thickness entails an increase  
 515 in the diffusion length for the ions, and therefore, the flux of  
 516 oxalate ions that reach the o/e interface is reduced according to  
 517 eqs 2 and 3. The change of  $j_{\text{L}}$  with the membrane thickness and  
 518 its dependence on  $t_{\text{BL}}$  can be understood in the frame of the  
 519 proposed HA mechanism. The lower the rate at which the  
 520 oxalate ions reach the o/e interface, the higher the amount of  
 521 ejected  $\text{Al}^{3+}$  ions that do not form complexes and hence  
 522 contribute to the formation of alumina or aluminum hydroxides  
 523 at this interface, resulting in an increase of  $t_{\text{BL}}$  and in a  
 524 reduction of the effective electric field across it. Consequently,  
 525 the migration of  $\text{O}^{2-}$  and  $\text{OH}^-$  across the barrier layer and thus  
 526 the current density are also reduced, according to eq 1.

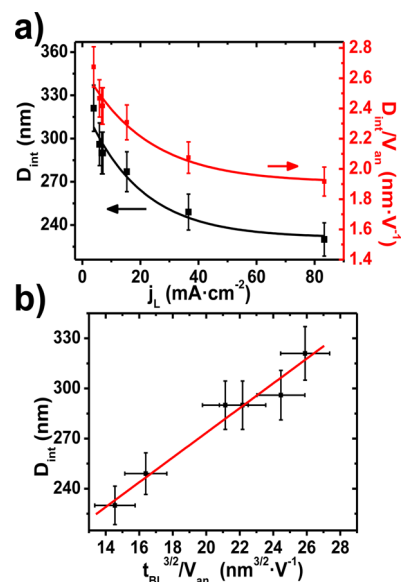
527 **Analysis of Interpore Distance, Pore Diameter, and**  
 528 **Self-Organization in HA.** On the basis of the analysis of SEM  
 529 bottom views of H-AAO membranes grown in 0.300 M oxalic  
 530 acid electrolytes at 120 V (Figure 5), we have studied the  
 531 variation of the interpore distance as well as the evolution of  
 532 the pore self-organization with the time duration of the  
 533 anodization process. The pore ordering degree in the HA-AAO  
 534 layer is low at the beginning of the potentiostatic HA process,  
 535 as can be seen in Figure 5a. However, the pore distribution  
 536 rapidly achieves a highly ordered hexagonal pore arrangement  
 537 that holds for HA durations between 5 and 240 min (Figures  
 538 5b–e).

539 Finally, for very long HA process (Figure 5f) the pore  
 540 arrangement turns into a randomly distributed form. The 540



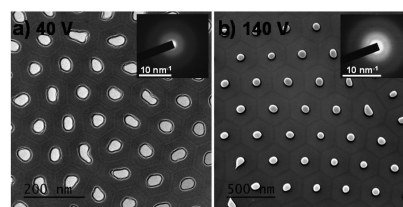


**Figure 5.** SEM images of the pore bottom of H-AAO membranes synthesized at 120 V in oxalic acid 0.300 M electrolytes containing 5 vol % of ethanol, during different anodization times, ranging from 0 to 36000 s.



**Figure 6.** (a) Dependence of the interpore distance,  $D_{int}$ , and the ratio of the interpore distance to anodizing voltage,  $D_{int}/V_{an}$ , on the limit current density,  $j_L$ , for H-AAO membranes anodized at 120 V in 0.300 M oxalic acid containing 5 vol % of ethanol. (b) Variation of  $D_{int}$  against  $t_{BL}^{3/2}/V_{an}$  for the same set of samples.

A comparison of TEM studies for both MA and HA-AAO membranes, performed after reducing the sample thickness by ion-milling thinning, is presented in Figure 7. The morpho-



**Figure 7.** TEM images of AAO membranes fabricated in 0.300 M oxalic acid electrolytes. (a) M-AAO, anodized at 40 V. (b) H-AAO, anodized at 140 V. The respective insets show the SAED spectra of each sample.

logical structure of both types of membranes is similar, and it is characterized by the self-ordered hexagonal pore arrangement. Furthermore, the presence of two alumina layers is observed: a contaminated alumina layer located in the region adjacent to the pores, and a purer alumina layer placed in between of two adjacent pores. In both cases, an amorphous structure is evidenced by the respective selected area electron diffraction (SAED) images displayed as insets in Figure 7.<sup>64–66</sup> However, a clear difference in the ratio of pore diameter,  $D_p$ , to  $D_{int}$  can be observed when comparing M-AAO and H-AAO membranes. While M-AAO have large pores in comparison to the interpore distance, thus resulting in an average  $D_p/D_{int}$  ratio of 0.35, H-AAO membranes present relatively narrow pores separated by larger distances, thus resulting an averaged ratio of 0.23. This reduction in the  $D_p$  to  $D_{int}$  ratio also implies lower porosity values in H-AAO than those found in M-AAO membranes fabricated under self-ordering conditions, in good agreement with previous studies.<sup>2,20,42</sup> The pore diameter shrinking with respect to the interpore distance observed in H-AAO membranes could also be related to the formation of an

reduction of the nanopore self-ordering degree can be attributed to the decrease of both, the electric field strength and its spatial distribution gradient, as a consequence of the increased barrier layer thickness in thick H-AAO layers, therefore resulting in a decrease of the anodization current density, as experimentally measured. This behavior is similar to that reported for M-AAO films, in which the ordering degree of the nanopore arrangement first increases due to self-ordering phenomena,<sup>5,60</sup> but afterward, it decreases again for long time duration anodization processes.<sup>42</sup>

The change of the interpore distance,  $D_{int}$ , with the final anodization current density,  $j_L$ , during HA is plotted in Figure 6a. These results indicate that  $D_{int}$  does not remain constant during the whole HA process but that it decreases exponentially with  $j_L$ , in good agreement with previous works.<sup>10,20,23,61</sup> Therefore, contrary to the case of MA, the ratio  $D_{int}/V_{an}$  is not constant during HA processes, taking values close to 2 nm·V<sup>-1</sup> for high  $j_L$  but increasing up to 2.7 nm·V<sup>-1</sup> as the final anodization current density is reduced during long HA steps.

The variation of  $D_{int}$  can be related to the thickening of  $t_{BL}$  with the anodization time as a result of the depletion of oxalate ions in HA processes. Indeed, in the frame of the viscous-flow model for the growth of nanoporous alumina,<sup>62,63</sup>  $D_{int}$  has been predicted to be proportional to  $t_{BL}^{3/2}/V_{an}$  (see Supporting Information). Figure 6b plots  $D_{int}$  against  $t_{BL}^{3/2}/V_{an}$ , indicating that the experimental data can be well fitted by a linear equation with a slope of 7.3 V·nm<sup>-1/2</sup>. This value is in good agreement with the viscous-flow model, which postulates an electrostatic energy-induced surface instability as the mechanism controlling pore interspacing in anodic oxide films (see discussion in Supporting Information). Despite this remarkable good agreement between the experimental data and predictions coming from this last theory, to favor unambiguously the viscous-flow model against the field-assisted dissolution one is not possible with the available data.

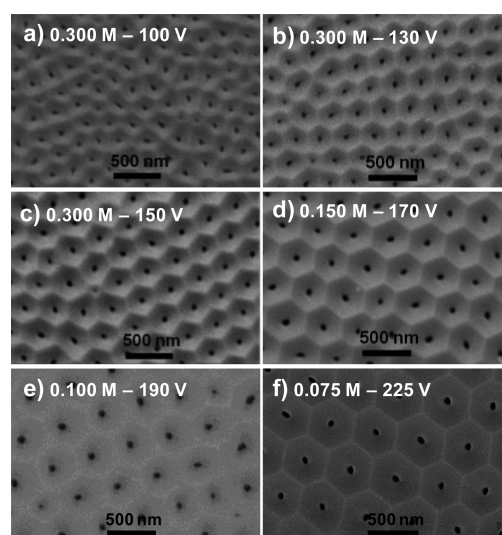
599 alumina layer in the o/e interface as a consequence of the  
600 depletion of oxalate ions in the pore bottom. Therefore, it is  
601 consistent with the proposed diffusion limited mechanism as  
602 the characteristic feature of HA processes.

603 The fact that HA is a diffusion-limited process and that  
604 therefore the concentration of reactive chemical species at the  
605 o/e interface is negligible suggests that the concentration of  
606 oxalic acid in the bulk of the electrolyte should not be a key  
607 factor governing the self-ordering of the nanopores in H-AAO  
608 membranes. This is a remarkable difference with the case of M-  
609 AAO ones, where highly ordered porous arrangements have  
610 been obtained only in a limited number of electrolytes and in a  
611 relatively narrow range of concentrations and applied anodic  
612 potentials for each specific electrolyte.<sup>43,66</sup> This fact motivated a  
613 study of the self-ordering regimes during HA of Al that will be  
614 discussed in the following section.

615 **Establishment of Self-Ordering Regimes in Hard**  
616 **Anodization of Aluminum through Voltammetric Stud-**  
617 **ies.** On the basis of the voltammograms obtained for oxalic acid  
618 electrolytes with different concentrations, we have synthesized a  
619 set of H-AAO membranes covering the whole voltage range  
620 comprising  $V_{HA}$  and  $V_{BD}$  for each electrolyte (see Table 1). In  
621 order to verify the self-ordered spatial arrangement of the  
622 nanopores grown during HA processes, the back of the alumina  
623 membranes was checked by SEM, after removing the aluminum  
624 substrate and the alumina barrier layer occluding the pore  
625 channels. Image analysis, performed by employing self-  
626 correlation function<sup>35,36</sup> allows us to determine the best self-  
627 ordering conditions for each electrolyte. The complete batch of  
628 samples fabricated in 0.150 M oxalic acid electrolyte containing  
629 5 vol % of ethanol at HA voltages ranging from 120 to 170 V, is  
630 shown in Figure S2 (see Supporting Information).

631 Even though all samples exhibit short-range porous spatial  
632 self-ordering, the larger self-ordered pore domains (size around  
633  $12 \mu\text{m}^2$ ) with hexagonal symmetry are found for the sample  
634 synthesized at 170 V. A similar study was performed for all  
635 samples anodized during 1.5 h at voltages ranging from 100 to  
636 225 V in 0.075–0.300 M oxalic acid electrolytes containing 5–  
637 10 vol % of ethanol, and some selected bottom-view SEM  
638 images are shown in Figure 8.

639 Figure 8a corresponds to a bottom-view of a H-AAO  
640 membrane obtained by hard anodization in 0.300 M oxalic acid  
641 electrolyte at 100 V, which corresponds to the  $V_{HA}$  value for  
642 this electrolyte (see Figure 2b). At this value of the anodization  
643 voltage, close to the beginning of the HA regime, the pores  
644 follow a random distribution at the bottom surface of the  
645 alumina membrane. The spatial ordering degree of the  
646 nanopore arrangement is clearly improved by increasing the  
647 anodization voltage, as can be seen in the micrographs of Figure  
648 8b and c, obtained at 130 and 150 V, respectively. Similar  
649 results were obtained for all the electrolytes with different oxalic  
650 acid concentrations studied in this work (see Figure 8d–f). For  
651 all of them, it was possible to find an interval of HA voltages at  
652 which the nanopores exhibit a self-ordered spatial distribution  
653 with hexagonal symmetry. At the same time, if the HA voltages  
654 are too near to the  $V_{HA}$  value for a given oxalic acid  
655 concentration, the hard-anodic samples exhibit worse pores  
656 ordering than those obtained at higher anodization voltages,  
657 much closer to  $V_{BD}$ . Therefore, a good spatial ordering degree  
658 of the nanopores can be achieved when  $V_{HA} \ll V_{an} < V_{BD}$ ; in  
659 good agreement with previous works that reported pore self-  
660 organization for anodization voltages close to the breakdown  
661 potential.<sup>1,67,68</sup>



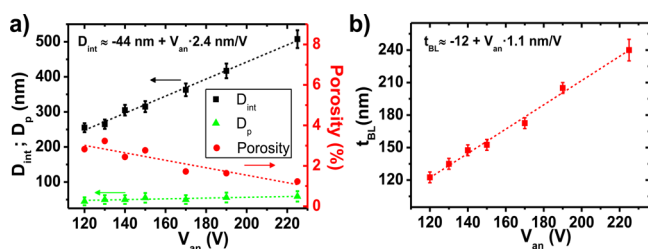
**Figure 8.** SEM images at the bottom surface of H-AAO membranes synthesized by hard anodization in oxalic acid electrolytes with different acid concentrations and under different anodization voltages of (a) 100 V, 0.300 M; (b) 130 V, 0.300 M; (c) 150 V, 0.300 M; (d) 170 V, 0.150 M; (e) 190 V, 0.100 M; and (f) 225 V, 0.075 M.

662 By correlating the given voltage values for the  $B^*$  interval in  
663 Table 1 with the SEM images of Figure 8, it can be seen that  
664 pore self-ordering conditions for each electrolyte were obtained  
665 at a certain HA voltage value that fits into the  $B^*$  range. In  
666 other words, the HA voltages leading to spatially self-ordered  
667 pore growth for all the tested oxalic acid concentrations fall into  
668 the plateau observed in the respective voltammograms (see  
669 Figure 3). In addition, our method based on voltammetric  
670 studies of the anodic oxidation of Al for the determination of  
671 the self-ordering HA conditions can be extended to other  
672 electrolytes, such as oxalic acid electrolytes containing ethylene  
673 glycol as an additive, as explained in detail in the Supporting  
674 Information and illustrated in Figure S3, which are interesting  
675 due to their stabilizing effect in the HA processes.

676 The reason for the correspondence between the current  
677 plateau observed in the voltammograms and the spatial self-  
678 ordering of the nanopores during HA processes remains still  
679 not fully understood. It could be related to a current  
680 compensation by the increase of the effective reaction surface,  
681 as a consequence of the formation of dissipative structures as  
682 proposed by Pashchanka and Schneider.<sup>69,70</sup> This phenomenon  
683 may be responsible for pore rearrangement following a  
684 hexagonally centered structure that maximizes the packing  
685 density of the nanopores.

686 The dependence of the interpore distance, pore diameter,  
687 and porosity on the HA voltage for all the self-ordered H-AAO  
688 membranes studied in this section is shown in Figure 9a. Figure  
689 9b depicts the dependence of the alumina barrier layer  
690 thickness on  $V_{an}$ . A linear relationship of both  $D_{int}$  and  $t_{BL}$  on  
691 the anodization voltage was found for these samples, anodized  
692 under HA conditions during 1.5 h, resulting in proportionality  
693 constants of about  $2.4 \text{ nm}\cdot\text{V}^{-1}$  and  $1.1 \text{ nm}\cdot\text{V}^{-1}$  for  $D_{int}$  and  $t_{BL}$ ,  
694 respectively. It is worth mentioning that the linear relationship  
695 between  $D_{int}$  and  $t_{BL}$  on the anodization voltage is only  
696 obtained under particular experimental conditions, in view that  
697 both geometrical parameters of H-AAO membranes depend  
698 not only on the anodization voltage but also on the anodization





**Figure 9.** (a) Dependence of the inter pore distance,  $D_{int}$ , pore diameter,  $D_p$ , and estimated porosity on the hard anodization voltage for H-AAO membranes obtained in oxalic acid electrolytes with concentrations ranging from 0.075 to 0.300 M. (b) Dependence of the alumina barrier layer thickness,  $t_{BL}$ , on the anodization voltage for the same H-AAO membranes presented in panel a. The solid data-points represent experimental values, whereas the dashed lines represent the respective linear fits of the experimental data.

699 time and membrane thickness, as previously discussed.  
700 Therefore, the different proportionality constants between  
701  $D_{int}$  and  $V_{an}$  reported in the literature<sup>2,8,10,20</sup> can be ascribed to  
702 different membrane thicknesses and experimental synthesis  
703 conditions employed in these works.

704 Despite the remarkable large and continuous variation in  $D_{int}$   
705 and  $t_{BL}$  with  $V_{an}$ ,  $D_p$  keeps at an almost constant value of  
706 around 50–60 nm for all of the H-AAO membranes studied  
707 here. As can be observed in Figure 9a, the independence of  
708 pore diameter,  $D_p$ , on the anodization voltage allows one to  
709 modify the porosity of the H-AAO layers, estimated as  $P = 100 \cdot$   
710  $(\pi/2) \cdot 3^{-1/2} (D_p/D_{int})^2$ ,<sup>42</sup> while keeping the good ordering  
711 degree of the nanopores, contrary to the case of M-AAO for  
712 which the porosity is limited to values of about 10%<sup>42</sup> or higher,  
713 if it is desired to keep the spatial nanopores ordering of the  
714 alumina membrane. This novel finding provides additional  
715 flexibility for the design of tailored nanoporous membranes for  
716 their use as templates, allowing for the independent tuning of  
717 pore diameter and inter pore distance.

718 It is worth noting that the quest for the self-ordering regimes  
719 during Al anodization is usually performed by trial and error  
720 methods, which is time-consuming and expensive. The method  
721 presented here allows one to perform a preliminary selection of  
722 the anodic conditions, appropriately chosen from the study of  
723 the LSV curves, which can lead to an optimum self-ordered  
724 nanopore arrangement for a given electrolyte concentration.  
725 Therefore, this approach results in a more efficient and time-  
726 saving fabrication technique.

## 727 ■ CONCLUSIONS

728 The anodic oxidation of Al under HA conditions in oxalic acid  
729 electrolytes with different concentrations has been studied in  
730 detail by performing LSV experiments and systematic character-  
731 ization of the morphological parameters of H-AAO ( $D_{int}$ ,  $D_p$ ,  
732 and  $t_{BL}$ ) and their variation as a function of the HA membrane  
733 thickness and the anodization current density. The results allow  
734 us to conclude that HA processes in oxalic acid electrolytes are  
735 mainly governed by the diffusion of oxalate ions through the  
736 pore channels from the bulk of the electrolyte to the pore  
737 bottom, according with our phenomenological model. The  
738 depletion of oxalates at the bottom of the pores causes an  
739 increase of the alumina barrier layer thickness due to the  
740 redeposition of the  $Al^{3+}$  ions ejected into the electrolyte during  
741 Al anodization, which, in the case of HA processes, contributes  
742 to the growth of alumina in the oxide/electrolyte interface. This

fact might be the key difference between the MA and the HA  
regimes.

The study of HA processes in electrolytes with different  
oxalic acid concentrations for a wide variety of anodization  
voltages allowed us to determine the best self-ordering  
conditions for each electrolyte concentration that give rise to  
highly ordered spatial distributions of pores during HA  
processes. Our results indicate that, by carefully adjusting the  
conditions of the HA processes, it is possible to produce  
hexagonally self-ordered nanopore arrangements exhibiting a  
large range of available inter pore distances (240–507 nm),  
while keeping the pore diameter almost constant (50–60 nm),  
thus allowing for a continuous tuning of the membrane  
porosity.

Additionally, voltammetric analysis of the anodic oxidation of  
Al, which has been applied to the HA of Al for the first time in  
this work to the best of our knowledge, allows us to distinguish  
from the mild and the hard anodization regimes for any  
electrolyte. Furthermore, the correspondence found between  
the self-ordering anodization voltage and the current plateau  
observed in the LSV for each one of the different electrolytes  
tested in this work provides a powerful method to determine, in  
a time-saving manner, the HA conditions that might lead to  
highly spatially ordered nanoporous arrangements. This  
method was also successfully applied to an electrolyte  
composed of 0.300 M oxalic acid and 50 vol % of ethylene  
glycol, thus demonstrating its flexibility of implementation in  
other electrolytes and paving the way for extensive research of  
the pores self-ordering conditions in more complex electrolytes.  
Furthermore, our study may open the door for innovative  
anodization protocols allowing for the preparation of H-AAO  
membranes keeping constant pore density values, by  
controlling the anodization parameters and electrolyte concen-  
tration, in order to compensate for the diffusion length increase  
due to the fast growth of H-AAO membranes.

## ■ ASSOCIATED CONTENT

### Supporting Information

The Supporting Information is available free of charge on the  
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Additional experimental results and discussions (PDF)

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### Notes

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